

EAST - [10.830046.wsp:1]

FileViewEditToolsWindowHelp

Active

L1: (11738) ferroelectric adj3 (memory or capacitor)

L2: (89993) bitline or digitline or columnline or bit-line or column-line or ((bit...

L3: (208772) (potential or voltage) adj3 generat\$4

L5: (238890) (drop\$4 or decreas\$4) near5 (potential or voltage)

L6: (476833) (rise or increas\$4) near5 temperature

L7: (6977) 5 same 6

L8: (361) 3 same 7

L9: (2) 1 same 8

L19: (25) 1 same 7

L22: (112) 1 same 6

L23: (24) 3 and 22

L24: (5) 1 and 8

L26: (2296) 365/146

L26: (211) 365/211

L27: (142) 365/212

L28: (3296) 365/189.09

L29: (4398) 365/226

L30: (3) 8 and 25

L31: (7) 8 and 26

L32: (3) 8 and 27

L33: (9) 8 and 28

L34: (6) 8 and 29

L35: (1610) 3 same 6

L36: (9) 1 and 35

L37: (4) 35 and 26

L39: (86) 2 and 35

L40: (770) 6 and 35

L41: (92) 40 and "365"/\$6

Failed

Saved

Favorites

Tagged (4)

UDC

Queue

Trash

Search:ListSourceQueryData

DB:US-PGPIB, USPAT; EPO, JPO, DERVENT; IBM, IDS

Default operator: OR

Plots

Highlight all hits initially

BRS form

ISIR form

Image

Text

HTML

	U	I	Q	Inventor	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval C	S	C	P	
1				Kuroda, Kenichi	US 5550770 A	19960827	78	Semiconductor memory device	365/145	267/E27.026;					

Hits

Details

HTML

NUM

Ready

BEST AVAILABLE COPY